

Notice of References Cited	Application No.	Applicant(s)
	08/691,434	Yamazaki et al.
	Examiner M. Wilczewski	Group Art Unit 1107

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*	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	5,304,357	4/1994	Sato et al.	----	----
B	4,475,027	10/1984	Pressley	----	----
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x O	64-76715	3/1989	JP	Sera	----	----
x P	2-73623	3/1990	JP	Aoyama et al.	----	----
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x u	Wagner et al., Formation of p-n Junctions and Silicides in Silicon Using a High Performance Laser Beam Homogenization System, Applied Surface Science, Vol. 43, 1989, pp. 260-263.	1989
x v	Jhon et al., Crystallization of Amorphous Silicon by Excimer Laser Annealing With a Line Shape Beam Having a Gaussian Profile, Jpn. J. Appl. Phys., Vol. 33, 1994, pp. L 1438-L 1441, Part 2, No. 10B, 15 October 1994.	1994
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* A copy of this reference is not being furnished with this Office action.
(See Manual of Patent Examining Procedure, Section 707.05(a).)